

ABSTRACT OF DISCLOSURE

A method for suppressing the cutting of bonds between organic radical (for example, CH_3 -radical) or H-radical and Si atom in SOG film during an ashing process, thereby maintaining a low dielectric constant, after wiring gutters are formed through etching on organic or inorganic SOG film of low dielectric constant using a patterned resist film(s) thereon as a mask, the resist film(s) is removed by treating with the ashing process by use of a plasma ashing apparatus of a sheet-fed down-stream type under an atmospheric pressure of 1.2 Torr, for example, and thereafter barrier metal is formed and Cu is filled into the wiring gutters, so as to form the wiring.

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